

Dual P-CHANNEL ENHANCEMENT MODE MOSFET
Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	I_D max
-20V	260m Ω @ $V_{GS} = -4.5V$	-0.9 A
	500m Ω @ $V_{GS} = -2.5V$	
	1000m Ω @ $V_{GS} = -1.8V$	

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Battery Disconnect Switch
- Load Switch for Power Management Functions

Features

- Low $R_{DS(on)}$ – Minimizes Conduction Losses
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

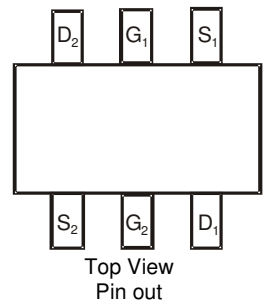
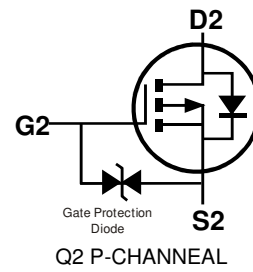
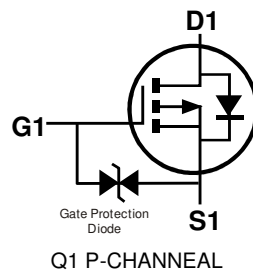
- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.006 grams (Approximate)



SOT363



Top View

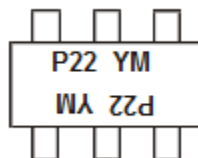

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2200UDW-7	SOT363	3,000/Tape & Reel
DMP2200UDW-13	SOT363	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com>.

Marking Information

SOT363



P22 = Marking Code
 YM = Date Code Marking
 Y or Y = Year (ex: B = 2014)
 M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020
Code	B	C	D	E	F	G	H

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±8	V
Continuous Drain Current (Note 6)	I _D	-0.9 -0.7	A
		T _A = +25°C T _A = +85°C	

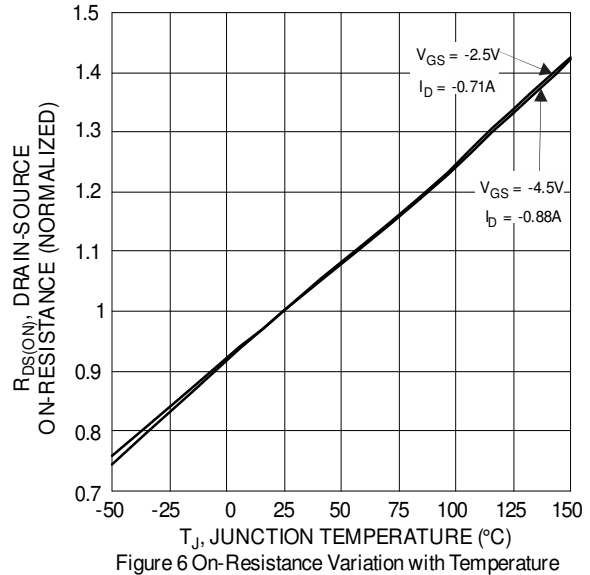
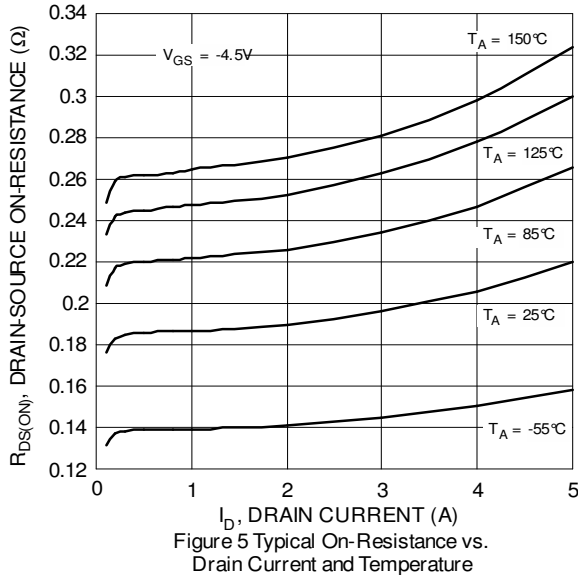
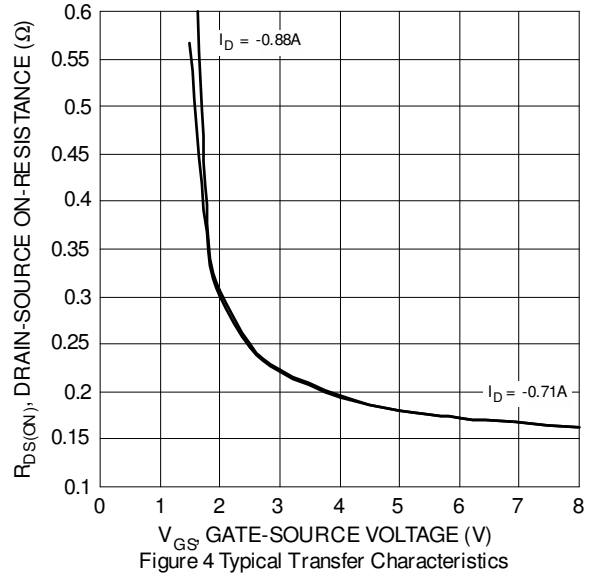
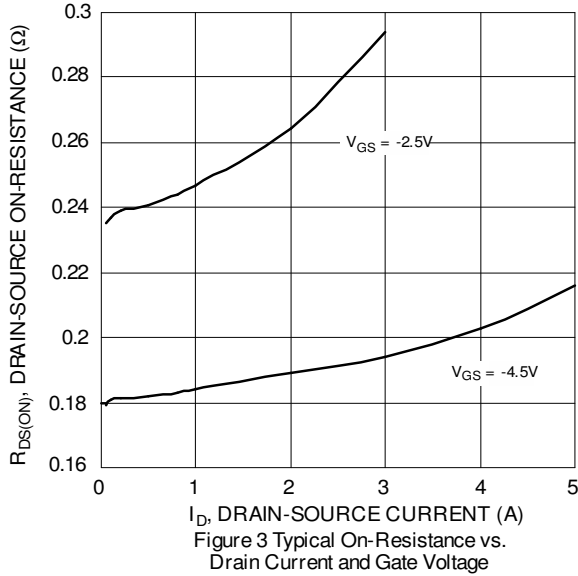
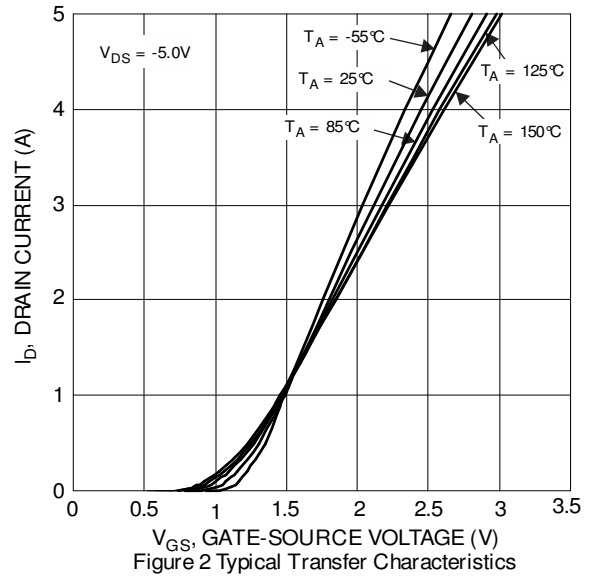
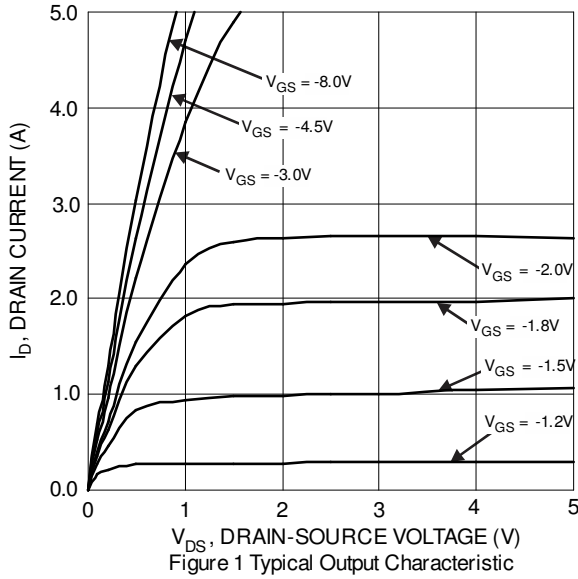
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

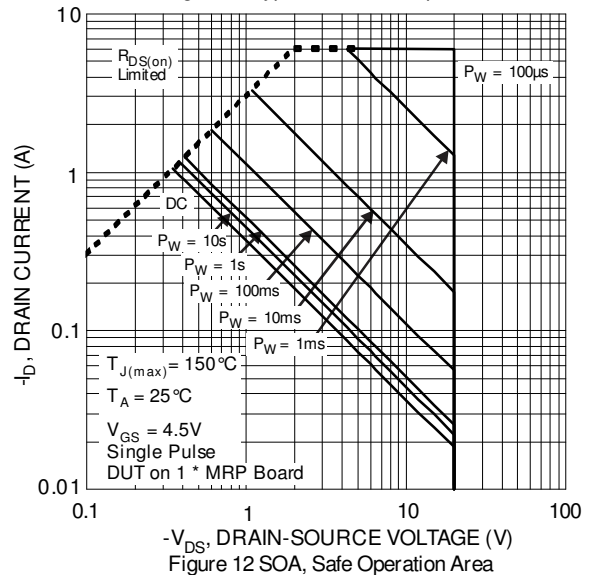
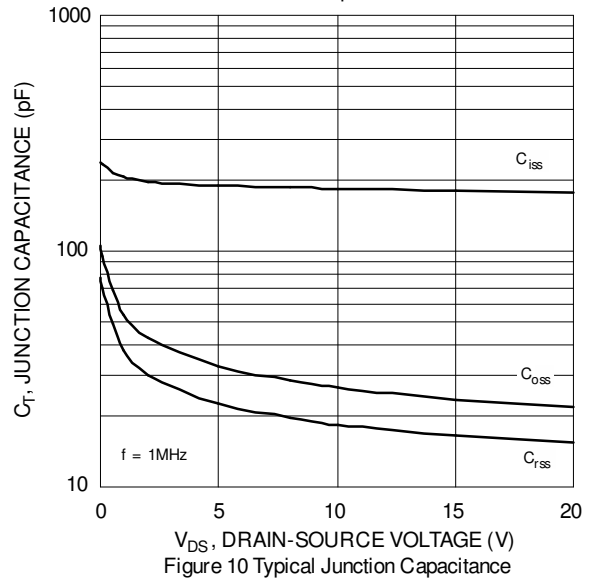
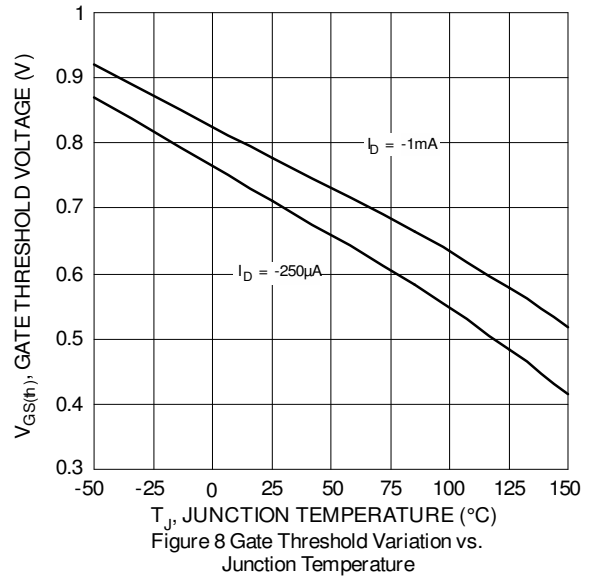
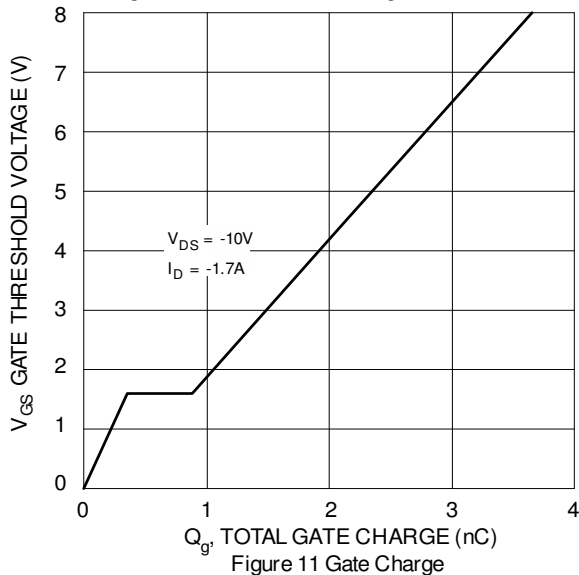
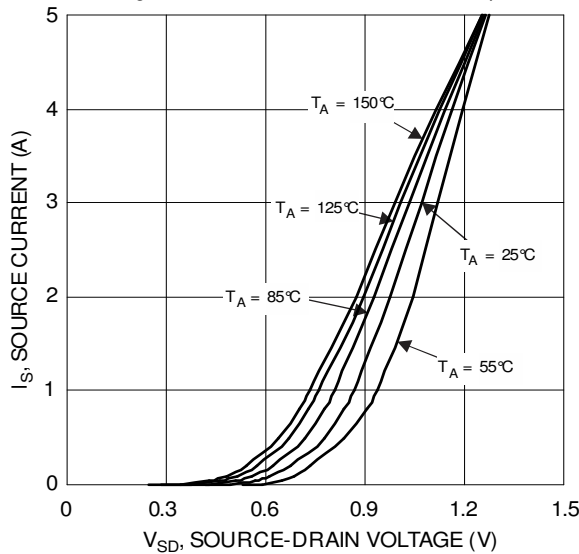
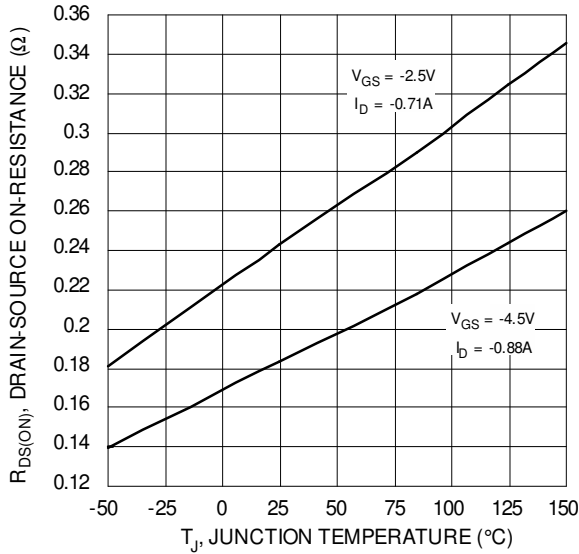
Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	0.45	W
Total Power Dissipation (Note 6)		0.6	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	275	°C/W
Thermal Resistance, Junction to Ambient (Note 6)		208	
Thermal Resistance, Junction to Case	R _{θJC}	72	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

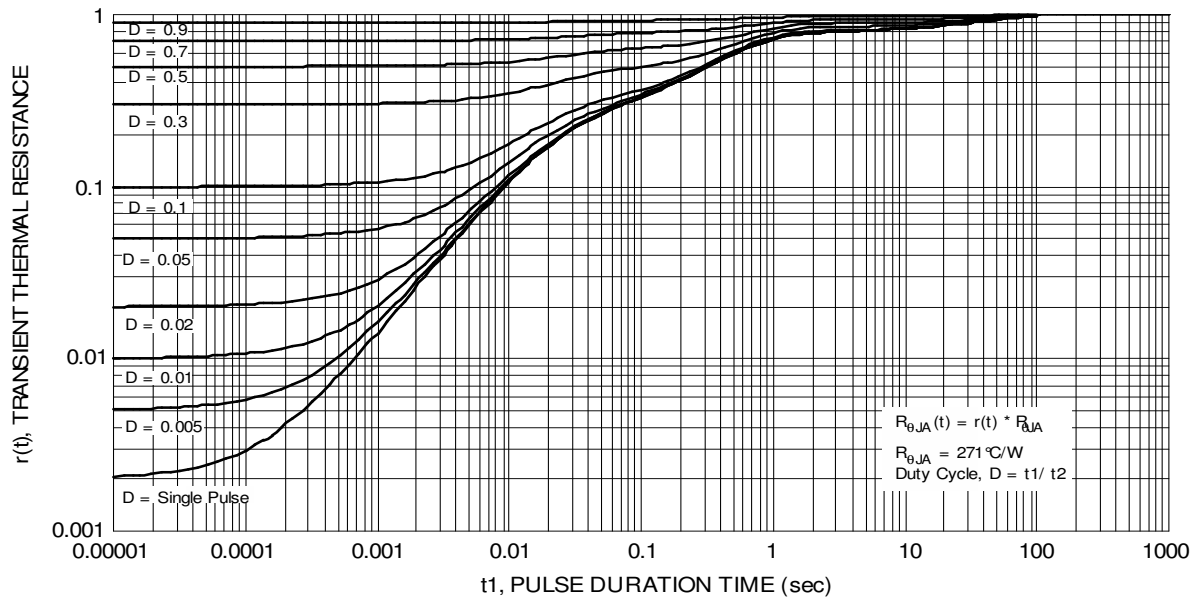
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -16V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-0.4	—	-1.2	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	180 240 320	260 500 1,000	mΩ	V _{GS} = -4.5V, I _D = -0.88A V _{GS} = -2.5V, I _D = -0.71A V _{GS} = -1.8V, I _D = -0.20A
Diode Forward Voltage	V _{SD}	—	-0.8	-1.2	V	V _{GS} = 0V, I _S = -0.48A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	184	—	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	26.4	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	18.5	—	pF	
Gate Resistance	R _g	—	221	—	Ω	V _{DS} = V _{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	—	2.1	—	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -1.7A
Gate-Source Charge	Q _{gs}	—	0.4	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.5	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	9.8	—	ns	V _{DD} = -10V, I _D = -1.5A, V _{GS} = -4.5V, R _{GEN} = 1Ω
Turn-Off Delay Time	t _{D(OFF)}	—	24.4	—	ns	
Turn-On Rise Time	t _r	—	88	—	ns	
Turn-Off Fall Time	t _f	—	45	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

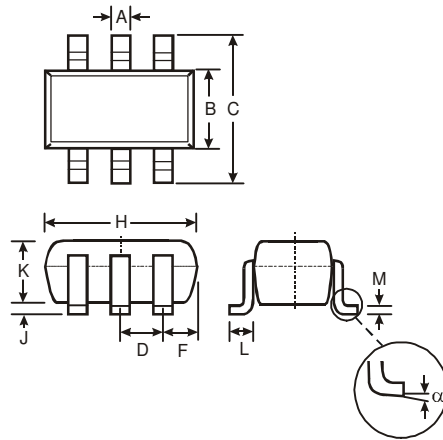






Package Outline Dimensions

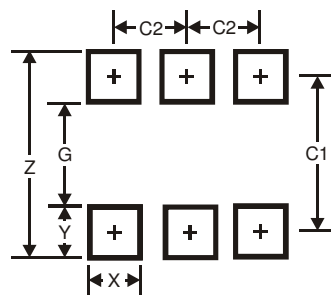
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT363			
Dim	Min	Max	Typ
A	0.10	0.30	0.25
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	0.65 Typ		
F	0.40	0.45	0.425
H	1.80	2.20	2.15
J	0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.22	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9